With gate a side

b side

.0 min

Unit: mm

Slit width

SEC. B-B

1: Anode

2-0.5

CNA1312K

Photo Interrupter

For contactless SW, object detection

Overview

CNA1312K is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

Features

- Ultraminiature: $2.6 \text{ mm} \times 4.9 \text{ mm}$ (height: 3.3 mm)
- Highly precise position detection: 0.1 mm
- Gap width: 2.0 mm

Abcolute Maximum Patings T 2500

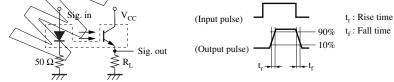
Absolute	Maximum Ratings	2 Cathode 3: Collector			
Parameter		Symbol	Rating	Unit	4: Emitter
Input (Light	Reverse voltage	V _R	6	V	PISSR104-002 Package (Note) 1. Tolerance unless otherwise specified is ±0.2
emitting diode)	Forward current	I _F	50	mA	2.() Dimension is reference
	Power dissipation *1	P _D	75	mW	V 3. * is dimension at the root of leads
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	35		
	Emitter-collector voltage (Base open)	V _{ECO}	6	/y \	
	Collector current	I _C	20 //	mA	Note) *1: Input power derating ratio is 1.0 mW/°C at
	Collector power dissipation *2	P _C	75	mW	$T_0 \ge 25^{\circ}$ C.
Temperature	Operating ambient temperature	T _{opr}	-25-to/+85	°C	*2: Output power derating ratio is 1.0 mW/°C at
	Storage temperature	T _{stg}	-40 to $+100$	°C	$T_a \ge 25^{\circ}C.$

$=25^{\circ}C \pm 3^{\circ}C$ Electrical-Optical Characteristics

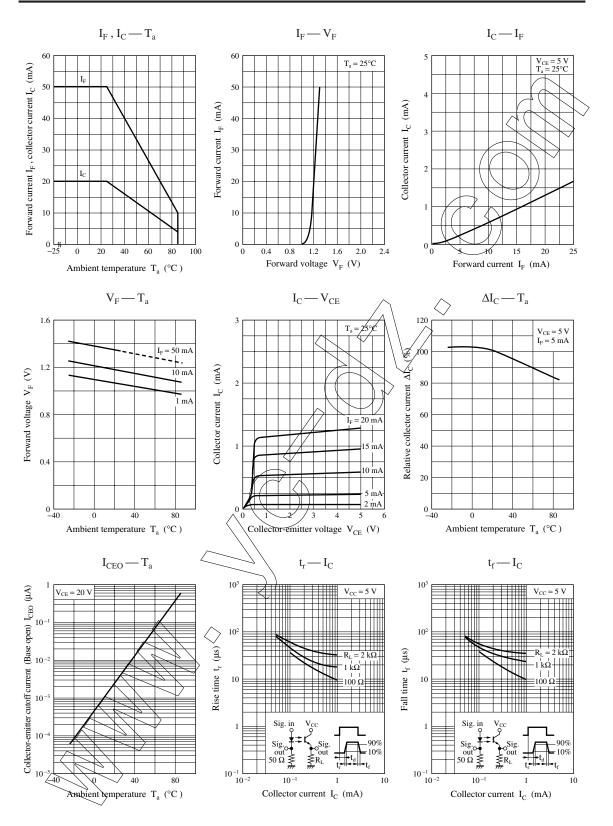
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V _F	$I_F = 20 \text{ mA}$		1.2	1.4	V
characteristics	Reverse current	I _R	$V_{R} = 3 V$			10	μΑ
Output	Collector-emitter cutoff current	I _{CEO}	$V_{CE} = 20 V$			100	nA
characteristics	(Base open)						
Transfer	Collector current	$\sum I_{C}$	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	40		400	μΑ
characteristics	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 10 \text{ mA}, I_C = 50 \mu\text{A}$			0.4	V
	Rise time *	t _r	$V_{CC} = 5 V, I_C = 0.1 mA$		50		μs
	Fall time*	t _f	$R_L = 1000~\Omega$		50		μs

Note) 1. Input and output are practiced by electricity.

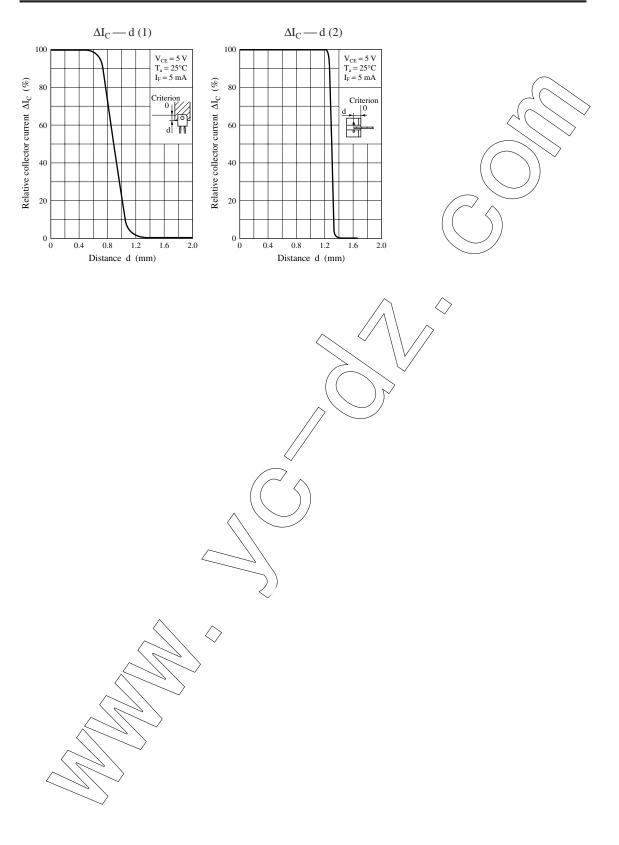
- 2. This device is designed be disregarded radiation.
- 3. *: Switching time measurement circuit



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A Caution for Safety

A DANGER

This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

Request for your special attention and precautions in using the technical information and semiconductors described in this material

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